L Number	Hits	Search Text	DB	Time stamp
1	211	shibata near2 kazutaka.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/10
2	137	(shibata near2 kazutaka.in.) and resin	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/10 10:28
3	17	((shibata near2 kazutaka.in.) and resin) and (polish\$4 or grind\$5)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/10 10:30
4	6	(((shibata near2 kazutaka.in.) and resin) and (polish\$4 or grind\$5)) and chip\$lon\$1chip	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/06/10 10:30
-	1569	resin same (polish\$ or grind\$) same (rear or back or back\$1side)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 16:49
-	755	resin same (polish\$ or grind\$) near10 (rear or back or back\$1side)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 16:49
-	318	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 16:49
-	50	resin nearl0 (polish\$ or grind\$) nearl0 (rear or back or back\$1side) same electrode	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 16:56
_	172	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) and semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 17:53
_	4 70	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) same chip	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 17:28
-	5 *	ichikawa.in. near2 kimiya and resin same semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 17:22
-	46	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) near20 expos\$	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 17:53
-	172	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) and semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 17:53
-	131	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$lside) and chip	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/18 18:12
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-	34	(rear or back or back\$1side) and chip) not ((resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) same electrode) or (resin near10 (polish\$ or grind\$) near10 (rear or back or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 10:17
		back\$1side) same chip) or (resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) near20 expos\$))		
-	192	resin near10 (polish\$4 or grind\$) near10 thick\$ and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 10:18
-	44	resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 11:26
_	262	resin near10 (polish\$4 or grind\$) same (back or back\$1side or rear) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 10:40
-	172	resin near10 (polish\$4 or grind\$) near10 (back or back\$1side or rear) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 10:40
-	133	(resin near10 (polish\$4 or grind\$) near10 (back or back\$1side or rear) and semiconductor) not (resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 10:41
-	7		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 11:28
_	54	resin near10 (polish\$4 or grind\$) near10 bottom and semiconductor not (resin near10 (polish\$4 or grind\$) near10 thick\$ same bottom and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 11:49
-	2	02153527.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 11:50
-	1216	etch\$ same (grind\$ or polish\$) same resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 13:02
-	150	etch\$ near10 (grind\$ or polish\$) near10 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 13:03
_	94	etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 13:05
-	38	(etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 13:06

-	2	6495914.pn.	USPAT;	2004/06/02
			US-PGPUB;	11:18
]			EPO; JPO;	
1			DERWENT;	
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-	0	chip adj on adj chip	USPAT;	2004/06/02
			US-PGPUB;	11:18
1			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	488	chip\$1on\$1chip	USPAT;	2004/06/02
			US-PGPUB;	11:19
1			EPO; JPO;	
	1		DERWENT;	1
	1		IBM TDB	
-	240	chip\$1on\$1chip near5 structure	USPAT;	2004/06/02
			US-PGPUB;	11:20
			EPO; JPO;	11.20
			DERWENT;	1
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_	32	chip\$1on\$1chip near5 structure same	USPAT;	2004/06/02
	32	electrode	US-PGPUB;	11:25
			EPO; JPO;	11:25
			DERWENT;	
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l _	54	chip\$lon\$lchip same resin	USPAT;	2004/06/02
	34	chippionpichip same resin		
			US-PGPUB;	11:44
			EPO; JPO;	
			DERWENT;	
_	25	chip\$1on\$1chip near10 advantag\$5	IBM_TDB	1 2224/26/22
	25	comparonations near 10 advantagas	USPAT;	2004/06/02
i			US-PGPUB;	11:59
			EPO; JPO;	]
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	4	5977640.pn.	USPAT;	2004/06/02
			US-PGPUB;	11:59
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!			DERWENT;	
			IBM_TDB	